





FEATURES

- · Visible light response
- Sintered construction
- · Low cost

DESCRIPTION

The **PDV-P8006** are (CdS), Photoconductive photocells designed to sense light from 400 to 700 nm. These light dependent resistors are available in a wide range of resistance values. They're packaged in a two leaded plastic-coated ceramic header.

APPLICATIONS

- Camera exposure
- · Shutter controls
- · Night light Controls

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V_{pk}	Applied Voltage		150	V
P _{d ∆po/∆t}	Continuous Power Dissipation		100	mW/°C
To	Operating and Storage Temperature	-30	+75	°C
Ts	Soldering Temperature*		+260	°C

^{* 0.200} inch from base for 3 seconds with heat sink.

ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _D	Dark Resistance	After 10 sec. @ 10 Lux @ 2856 °K	5			$\mathbf{M}\Omega$
R _I	Illuminated Resistance	10 Lux @ 2856 °K	80		240	ΚΩ
S	Sensitivity	LOG(R100)-LOG(R10)** LOG(E100)-LOG(E10)***		0.85		$\Omega/{\sf Lux}$
λ range	Spectral Application Range	Flooded	400		700	nm
λ peak	Spectral Application Range	Flooded		520		nm
t _r	Rise Time	10 Lux @ 2856 °K		60		ms
T _f	Fall Time	After 10 Lux @ 2856 °K		25		ms

^{**}R100, R10: cell resistances at 100 Lux and 10 Lux at 2856 °K respectively .

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.

^{***}E100, E10: luminances at 100 Lux and 10 Lux 2856 °K respectively.